

2SD1938FSL Datasheet



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DiGi Electronics Part Number 2SD1938FSL-DG

Manufacturer Panasonic Electronic Components

Manufacturer Product Number 2SD1938FSL

Description TRANS NPN 20V 0.3A MINI3

Detailed Description Bipolar (BJT) Transistor NPN 20 V 300 mA 80MHz 20

0 mW Surface Mount Mini3-G1



Tel: +00 852-30501935

RFQ Email: Info@DiGi-Electronics.com

DiGi is a global authorized distributor of electronic components.



Purchase and inquiry

Manufacturer Product Number:	Manufacturer:			
2SD1938FSL	Panasonic Electronic Components			
Series:	Product Status:			
	Obsolete			
Transistor Type:	Current - Collector (Ic) (Max):			
NPN	300 mA			
Voltage - Collector Emitter Breakdown (Max):	Vce Saturation (Max) @ lb, lc:			
20 V	100mV @ 3mA, 30mA			
Current - Collector Cutoff (Max):	DC Current Gain (hFE) (Min) @ Ic, Vce:			
100nA (ICBO)	500 @ 4mA, 2V			
Power - Max:	Frequency - Transition:			
200 mW	80MHz			
Operating Temperature:	Mounting Type:			
150°C (TJ)	Surface Mount			
Package / Case:	Supplier Device Package:			
TO-236-3, SC-59, SOT-23-3	Mini3-G1			
Base Product Number:				
2SD1038				

Environmental & Export classification

Moisture Sensitivity Level (MSL):	ECCN:
1 (Unlimited)	EAR99
HTSUS:	
8541 21 0095	

2SD1938(F)

Silicon NPN epitaxial planar type

For low-voltage output amplification For muting

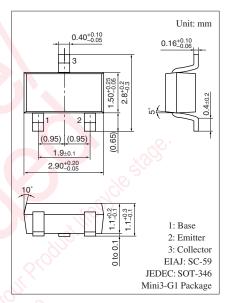
For DC-DC converter

■ Features

- Low ON resistance Ron
- High forward current transfer ratio h_{FE}
- Mini type package, allowing downsizing of the equipment and automatic insertion through the tape packing

■ Absolute Maximum Ratings $T_a = 25$ °C

Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	V_{CBO}	50	V
Collector-emitter voltage (Base open)	V_{CEO}	20	V
Emitter-base voltage (Collector open)	V_{EBO}	25	V
Collector current	I_{C}	300	mA
Peak collector current	I_{CP}	500	mA
Collector power dissipation	P _C	200	mW
Junction temperature	T_{j}	150	°C
Storage temperature	T_{stg}	-55 to +150	°C√0



Marking symbol: 3W

■ Electrical Characteristics $T_a = 25$ °C ± 3 °C

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-emitter voltage (Base open)	V _{CEO}	$I_C = 1 \text{ mA}, I_B = 0$	20			V
Base-emitter voltage	V_{BE}	$V_{CE} = 2 \text{ V}, I_C = 4 \text{ mA}$	10 J	0.6		V
Collector-base cutoff current (Emitter open)	I_{CBO}	$V_{CB} = 50 \text{ V}, I_{E} = 0$	7.7		0.1	μΑ
Emitter-base cutoff current (Collector open)	I_{EBO}	$V_{EB} = 25 \text{ V}, I_{C} = 0$			0.1	μΑ
Forward current transfer ratio *1	h _{FE}	$V_{CE} = 2 \text{ V}, I_C = 4 \text{ mA}$	500		2500	_
Collector-emitter saturation voltage	V _{CE(sat)}	$I_C = 30 \text{ mA}, I_B = 3 \text{ mA}$			0.1	V
Transition frequency	f_T	$V_{CB} = 6 \text{ V}, I_E = -4 \text{ mA}, f = 200 \text{ MHz}$		80		MHz
Collector output capacitance	C _{ob}	$V_{CB} = 10 \text{ V}, I_{E} = 0, f = 1 \text{ MHz}$			7	pF
(Common base, input open circuited)		18.02 NITH				
ON resistance *2	Ron	- Control of the cont		1.0		Ω

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

2. *1: Rank classification

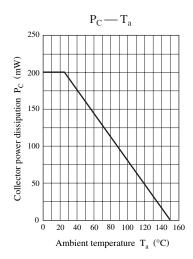
Rank	S	Т	No rank		
h_{FE}	500 to 1 500	800 to 2500	500 to 2500		

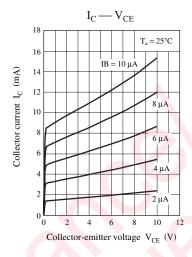
Product of no-rank classification is not marked.

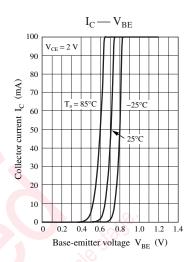
*2: R_{on} Measuremet circuit

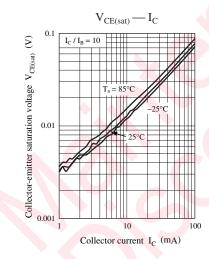
$$V_B$$
 V_V V_A V_B V_B V_A V_A V_B V_B V_A V_A V_B V_B V_A V_A

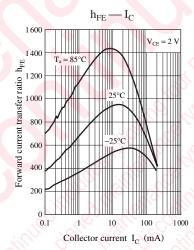
 $R_{\rm on} = \frac{V_{\rm B}}{V_{\rm A} - V_{\rm B}} \times 1000 \,(\Omega$

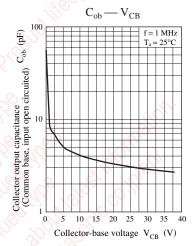












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